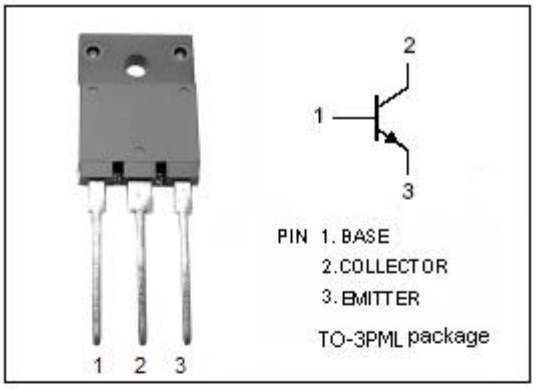
isc Silicon NPN Power Transistor — 2SC3896



DESCRIPTION

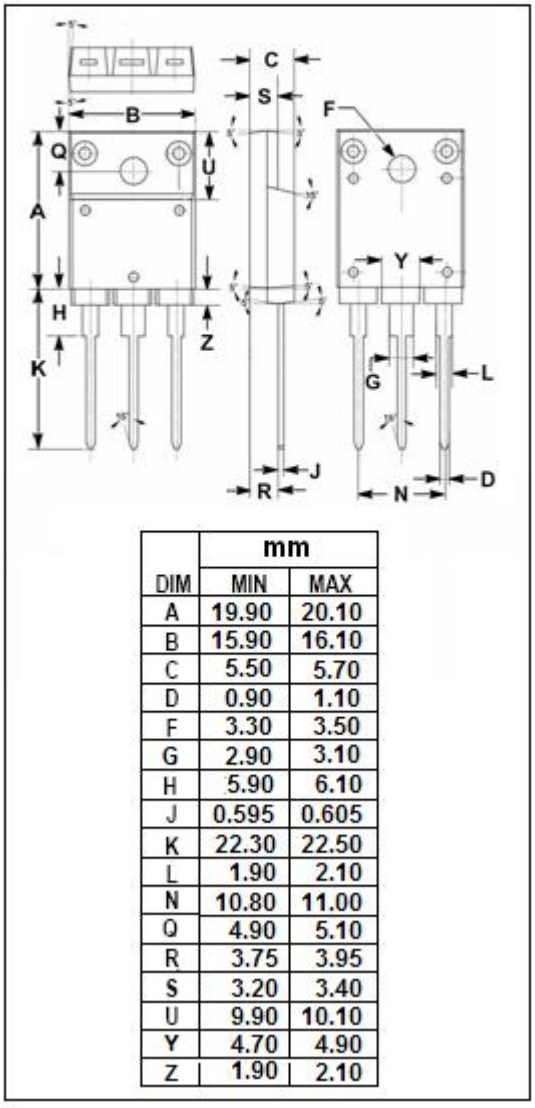
- High Breakdown Voltage
- High Switching Speed
- Wide Area of Safe Operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Ultrahigh definition CRT display horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	8	A
I_{CM}	Collector Current- Peak	25	A
P_C	Collector Power Dissipation @ T_C=25℃	70	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.90	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
H	5.90	6.10
J	0.595	0.605
K	22.30	22.50
L	1.90	2.10
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 1.2A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 1.2A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 800V; I_E= 0			100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}=4V; I_C= 0			100	uA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 5V	8			
h_{FE-2}	DC Current Gain	I_C= 6A; V_{CE}= 5V	4		8	
Switching times						
t_{stg}	Storage Time	I_C= 6A ;I_{B1}=1.2A; I_{B2}= -2.4A			3	μs
t_f	Fall Time				0.2	μs